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TRANSMITTAL FORM

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Total Number of Pages in This Submission

Application Number 10/689,958

Filing Date October 20, 2003

First Named Inventor Cem Basceri

Art Unit 2812

Examiner Name Unknown

Attorney Docket Number MI22-2417

ENCLOSURES (Check all that apply)

☐ Fee Transmittal Form

☐ Fee Attached

☐ Amendment/Reply

☐ After Final

☐ Affidavits/declaration(s)

☐ Extension of Time Request

☐ Express Abandonment Request

☒ Supplemental
Information Disclosure Statement

☐ Certified Copy of Priority
Document(s)

☐ Reply to Missing Parts/
Incomplete Application

☐ Reply to Missing Parts
under 37 CFR 1.52 or 1.53

☐ Drawing(s)

☐ Licensing-related Papers

☐ Petition

☐ Petition to Convert to a
Provisional Application

☐ Power of Attorney, Revocation

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☐ After Allowance Communication to TC

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☐ Proprietary Information

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Remarks

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Mark S. Matkin

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10/28/04

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32,268

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EV372470007



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No..... 10/689,958
Filing DateOctober 20, 2003
Inventor Cem Basceri
Assignee Micron Technology, Inc.
Group Art Unit 2812
Examiner Unknown
Attorney Docket No.....MI22-2417
Customer No.021567
Title: Methods of Forming Conductive Metal Silicides by Reaction of Metal with
Silicon

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449


The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S. patents or U.S. patent application publications are included, as the date of filing of this patent application occurs after June 30, 2003. Copies of all other references are attached. No admission is made regarding whether all the listed references are prior art.

Citation of the referenced art is respectfully requested.

This Information Disclosure Statement is being filed before the mailing date of a first Office Action. There, no fee is believed to be required. However, in the event that a fee is required for filing this Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 10-25-04

By: 
Mark S. Matkin
Reg. No. 32,268

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| Form PTO-1449 | | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | | | ATTY. DOCKET NO. MI22-2417 | | SERIAL NO. 10/689,958 | |
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| U.S. PATENT DOCUMENTS | | | | | | | |
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| | | | | | Yes | No | |
| AJ | EP 0 851 473 A2 | 01/1998 | EPO | | X | | |
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| AM | | Chang et al., Silicon surface treatments in advanced MOS gate processing, Microelectronic Engineering, (2004), pages 130-135 |
| AN | | Lemberger et al., Electrical characterization and reliability aspects of zirconium silicate films obtained from novel MOCVD precursors, Microelectronic Engineering (2004), pages 315-320 |
| AO | | Lu et al., Effects of the TaN _x interface layer on doped tantalum oxide high-k films, VACUUM (2004), pages 1-9 |
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